# PLASMA PROCESSING APPARATUS AND SUBSTRATE SUPPORT

## ABSTRACT

A plasma processing apparatus includes a plasma processing chamber, a base, a high frequency power supply, an electrostatic chuck, a joint portion, and a conductive layer. The base is disposed in the plasma processing chamber. The high frequency power supply is electrically connected to the base. The electrostatic chuck is disposed at an upper portion of the base and includes an attraction electrode. The joint portion joins the base and the electrostatic chuck. The conductive layer is disposed between the base and the attraction electrode. The base has an upper surface at which a heat transfer gas flow path defined by the base and the joint portion is formed. The conductive layer has a thickness equal to or larger than a skin depth at a frequency of high frequency power output by the high frequency power supply.

Figure 2